



80V 175°C N-CHANNEL ENHANCEMENT MODE MOSFET POWERDI®

Product Summary

BV _{DSS}	R _{DS(ON)}	I _D T _C = +25°C
80V	$17m\Omega @ V_{GS} = 10V$	72A
	$21m\Omega$ @ $V_{GS} = 4.5V$	62A

Description and Applications

This MOSFET is designed to minimize the on-state resistance (R_{DS(ON)}) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

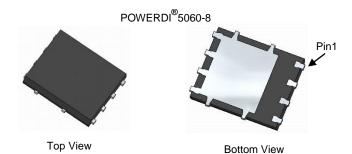
- Synchronous Rectifier
- Backlighting
- Power Management Functions
- DC-DC Converters

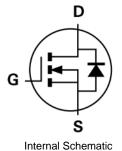
Features

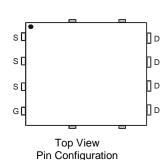
- Rated to +175°C Ideal for High Ambient Temperature Environments
- High Conversion Efficiency
- Low R_{DS(ON)} Minimizes On State Losses
- Low Input Capacitance
- · Fast Switching Speed
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

- Case: POWERDI[®] 5060-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Finish Matte Tin Annealed over Copper Leadframe;
 Solderable per MIL-STD-202, Method 208 (§3)
- Weight: 0.097 grams (Approximate)







Ordering Information (Note 4)

Part Number	Case	Packaging	
DMTH8012LPS-13	POWERDI [®] 5060-8	2,500 / Tape & Reel	

Notes:

- 1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
- 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and
- <1000ppm antimony compounds.

 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



☐ ☐ Hanufacturer's Marking
☐ H8012LS = Product Type Marking Code
☐ YYWW = Date Code Marking
☐ YY = Last Two Digits of Year
☐ (ex: 15 = 2015)
☐ WW = Week Code (01 to 53)

POWERDI is a registered trademark of Diodes Incorporated. $\label{eq:decomposition} DMTH8012LPS$

Document number: DS37589 Rev.2 - 2



Maximum Ratings ($@T_A = +25^{\circ}C$, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Drain-Source Voltage		V_{DSS}	80	V
Gate-Source Voltage		V_{GSS}	±20	V
Continuous Drain Current, V _{GS} = 10V (Note 5)	$T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$	I _D	10 8.4	А
Continuous Drain Current, V _{GS} = 10V (Note 6)	$T_C = +25$ °C $T_C = +70$ °C	I _D	72 60	А
Maximum Continuous Body Diode Forward Current (Note 6)		Is	90	Α
Pulsed Drain Current (10μs Pulse, Duty Cycle = 1%)		I _{DM}	80	Α
Avalanche Current, L=0.1mH		I _{AS}	11.6	А
Avalanche Energy, L=0.1mH		E _{AS}	10.2	mJ

Thermal Characteristics

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)	$T_A = +25$ °C	P_{D}	2.6	W
Thermal Resistance, Junction to Ambient (Note 5)		$R_{ heta JA}$	57	°C/W
Total Power Dissipation (Note 6)	$T_C = +25^{\circ}C$	P_{D}	136	W
Thermal Resistance, Junction to Case (Note 6)		$R_{ heta JC}$	1.1	°C/W
Operating and Storage Temperature Range		T _{J,} T _{STG}	-55 to +175	°C

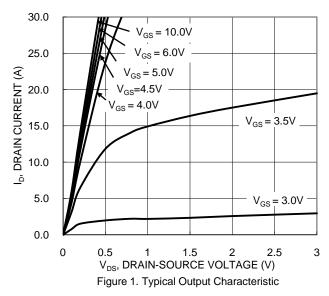
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)	,						
Drain-Source Breakdown Voltage	BV _{DSS}	80	-	-	V	$V_{GS} = 0V$, $I_D = 1mA$	
Zero Gate Voltage Drain Current	I _{DSS}	-	-	1	μΑ	$V_{DS} = 64V, V_{GS} = 0V$	
Gate-Source Leakage	I _{GSS}	1	-	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage	V _{GS(TH)}	1	-	3	V	$V_{DS} = V_{GS}$, $I_D = 250\mu A$	
Static Drain-Source On-Resistance	D	-	14	17	mΩ	$V_{GS} = 10V, I_D = 12A$	
Static Dialii-Source Off-Resistance	R _{DS(ON)}	1	16.5	21		$V_{GS} = 4.5V, I_D = 6A$	
Diode Forward Voltage	V_{SD}	1	0.9	1.2	٧	$V_{GS} = 0V, I_{S} = 20A$	
DYNAMIC CHARACTERISTICS (Note 8)							
Input Capacitance	C _{iss}	-	1949	-		$V_{DS} = 40V$, $V_{GS} = 0V$, $f = 1MHz$	
Output Capacitance	Coss	-	177	-	pF		
Reverse Transfer Capacitance	C _{rss}	-	10	-			
Gate Resistance	Rg	-	0.7	-	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$	
Total Gate Charge (V _{GS} = 4.5V)	Qg	=	15	-			
Total Gate Charge (V _{GS} = 10V)	Qg	-	34	-	nC	$V_{DS} = 40V, I_{D} = 12A$	
Gate-Source Charge	Q_{gs}	-	6	-	iiC		
Gate-Drain Charge	Q_{gd}	-	4.5	-			
Turn-On Delay Time	t _{D(ON)}	-	4.9	-		$V_{DD} = 40V, V_{GS} = 10V,$ $I_{D} = 12A, R_{G} = 1.6\Omega$	
Turn-On Rise Time	t _R	-	3.8	-			
Turn-Off Delay Time	t _{D(OFF)}	-	16.5	-	ns		
Turn-Off Fall Time	t _F	=	3.5	-			
Body Diode Reverse Recovery Time	t _{RR}	-	30.2	-	ns	1 124 di/dt 1004/0-	
Body Diode Reverse Recovery Charge	Q_{RR}	-	34.6	-	nC	$I_F = 12A$, di/dt = 100A/ μ s	

Notes:

- Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.
 Thermal resistance from junction to soldering point (on the exposed drain pad).
 Short duration pulse test used to minimize self-heating effect.
 Guaranteed by design. Not subject to product testing.





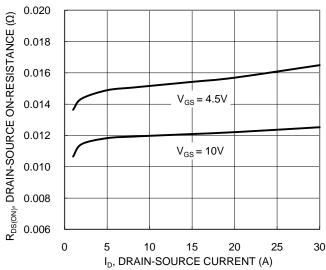


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

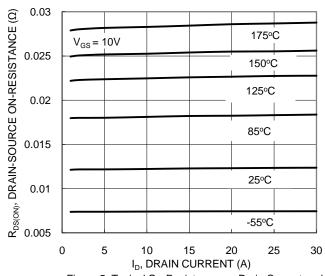
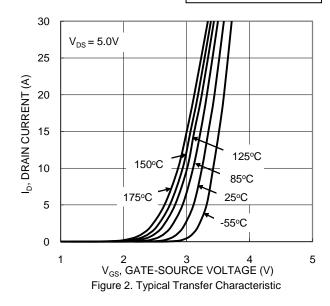
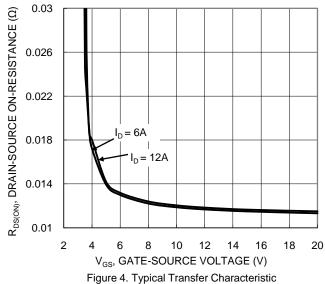


Figure 5. Typical On-Resistance vs. Drain Current and Temperature





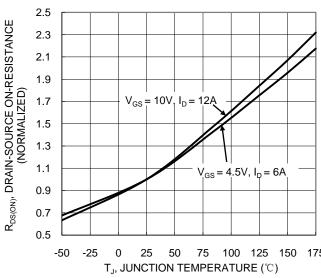


Figure 6. On-Resistance Variation with Temperature



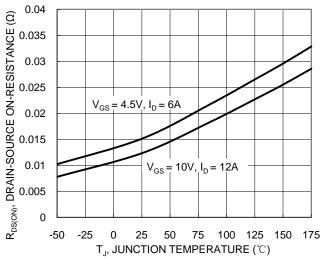


Figure 7. On-Resistance Variation with Temperature

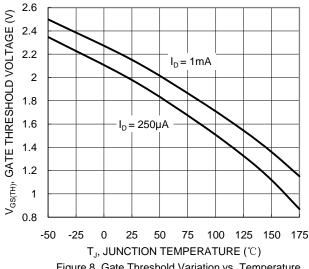
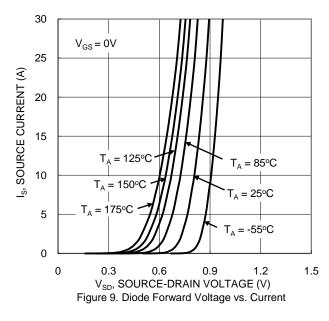
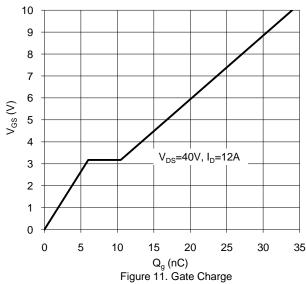
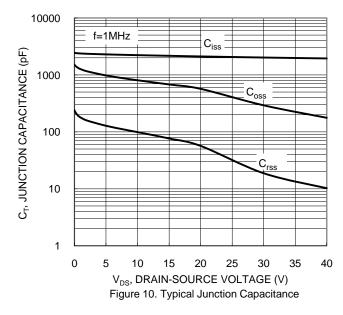
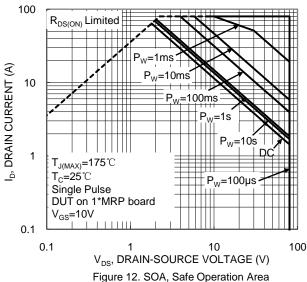


Figure 8. Gate Threshold Variation vs. Temperature

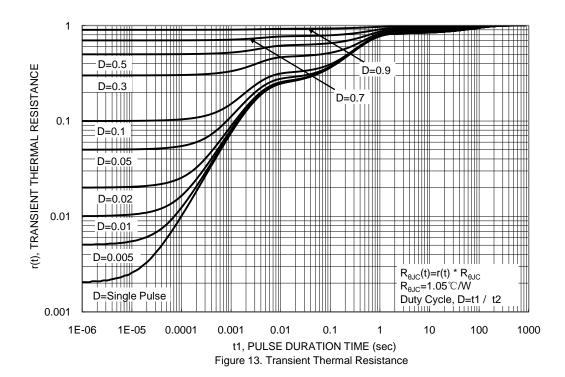










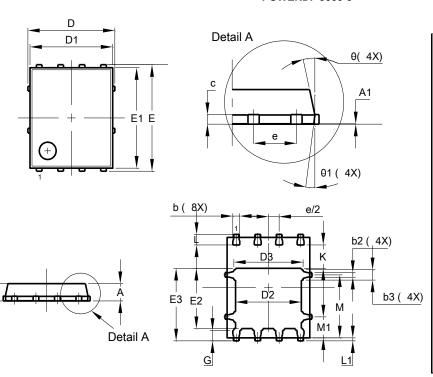




Package Outline Dimensions

Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.

POWERDI®5060-8

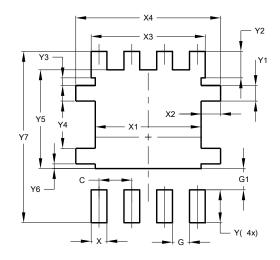


POWERDI®5060-8					
Dim	Min	Max	Тур		
Α	0.90	1.10	1.00		
A1	0.00	0.05	-		
b	0.33	0.51	0.41		
b2	0.200	0.350	0.273		
b3	0.40	0.80	0.60		
C	0.230	0.330	0.277		
D	Ļ	5.15 BSC	;		
D1	4.70	5.10	4.90		
D2	3.70	4.10	3.90		
D3	3.90	4.30	4.10		
Е	(3.15 BSC	;		
E1	5.60	6.00	5.80		
E2	3.28	3.68	3.48		
E3	3.99	4.39	4.19		
е	•	1.27 BSC			
G	0.51	0.71	0.61		
K	0.51	-	-		
L	0.51	0.71	0.61		
L1	0.100	0.200	0.175		
M	3.235	4.035	3.635		
M1	1.00	1.40	1.21		
θ	10°	12º	11º		
θ1	6°	8º	7º		
All Dimensions in mm					

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.

POWERDI[®]5060-8



Dimensions	Value (in mm)			
С	1.270			
G	0.660			
G1	0.820			
X	0.610			
X1	4.100			
X2	0.755			
Х3	4.420			
X4	5.610			
Y	1.270			
Y1	0.600			
Y2	1.020			
Y3	0.295			
Y4	1.825			
Y5	3.810			
Y6	0.180			
Y7	6.610			



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